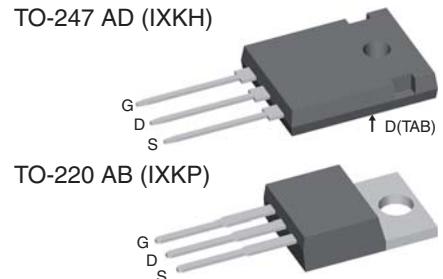
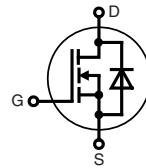


CoolMOS™ 1) Power MOSFET

N-Channel Enhancement Mode
Low $R_{DS(on)}$, High V_{DSS} MOSFET
Ultra low gate charge

I_{D25} = 20 A
 V_{DSS} = 600 V
 $R_{DS(on)\ max}$ = 0.2 Ω

**MOSFET**

Symbol	Conditions	Maximum Ratings		
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600		V
V_{GS}		± 20		V
I_{D25}	$T_C = 25^\circ\text{C}$	20		A
I_{D90}	$T_C = 90^\circ\text{C}$	13		A
E_{AS}	single pulse } E_{AR} repetitive } $I_D = 6.6 \text{ A}; T_C = 25^\circ\text{C}$	435		mJ
		0.66		mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50		V/ns

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}$		180	200
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 1.1 \text{ mA}$	2.5	3	3.5
I_{DSS}	$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		10	1
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100
C_{iss} C_{oss}	$V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$	1520 72		pF
Q_g Q_{gs} Q_{gd}	$V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 10 \text{ A}$	32 8 11	45	nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 10 \text{ A}; R_G = 3.3 \Omega$	10 5 50 5		ns
R_{thJC}			0.60	K/W

Features

- fast CoolMOS™ 1) power MOSFET
 - 4th generation
 - High blocking capability
 - Lowest resistance
 - Avalanche rated for unclamped inductive switching (UIS)
 - Low thermal resistance due to reduced chip thickness
- Enhanced total power density

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

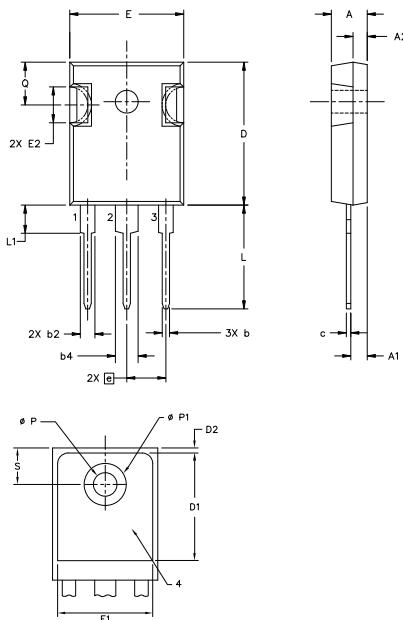
Source-Drain Diode

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.
I _s	V _{GS} = 0 V			10 A
V _{SD}	I _F = 10 A; V _{GS} = 0 V	0.9	1.2	V
t _{rr} Q _{RM} I _{RM}	I _F = 10 A; -di _F /dt = 100 A/μs; V _R = 400 V	340		ns
		5.5		μC
		33		A

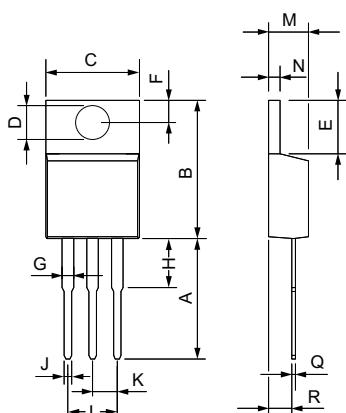
Component

Symbol	Conditions	Maximum Ratings		
T _{VJ}	operating	-55...+150	°C	
T _{stg}		-55...+150	°C	
M _d	mounting torque	0.8 ... 1.2 Nm		
	TO-247	0.4 ... 0.6 Nm		
	TO-220			

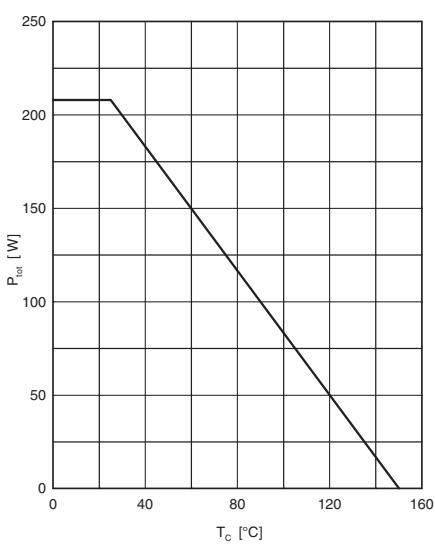
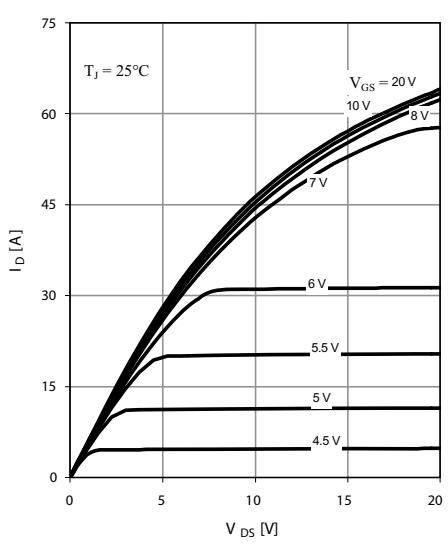
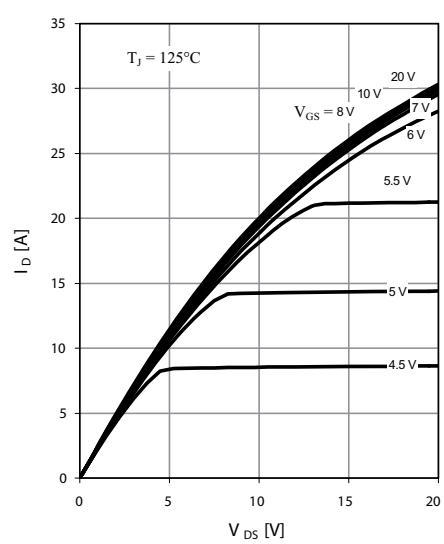
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R _{thCH}	with heatsink compound	0.25 K/W		
	TO-247	0.50 K/W		
	TO-220			
Weight	TO-247	6 g		
	TO-220	2 g		

TO-247 AD Outline


Symbol	Inches		Millimeters	
	min	max	min	max
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
OP	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
ØP1	-	0.291	-	7.39

TO-220 AB Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110


Fig. 1 Power dissipation

Fig. 2 Typ. output characteristics

Fig. 3 Typ. output characteristics

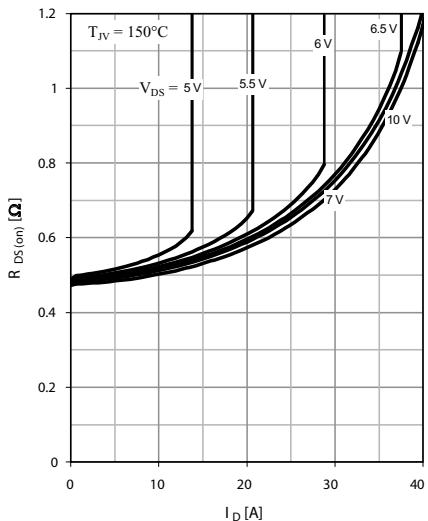


Fig. 4 Typ. drain-source on-state resistance characteristics of IGBT

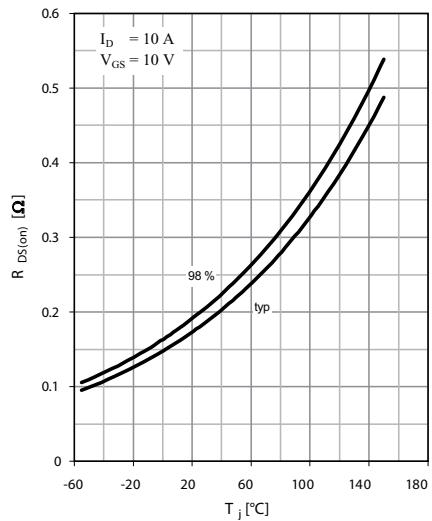


Fig. 5 Drain-source on-state resistance

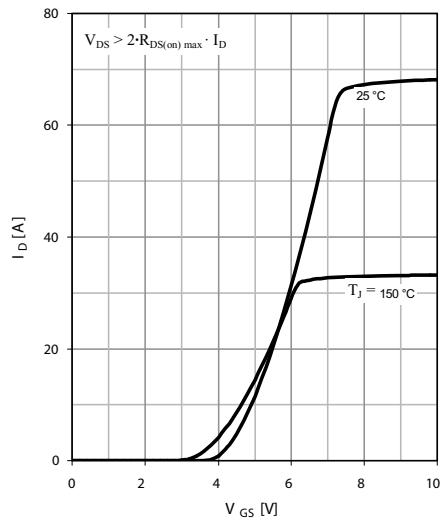


Fig. 6 Typ. transfer characteristics

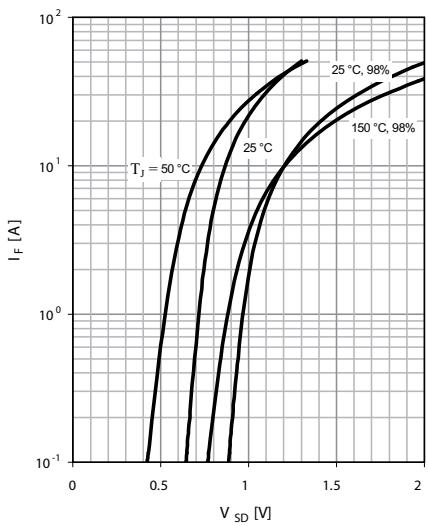


Fig. 7 Forward characteristic of reverse diode

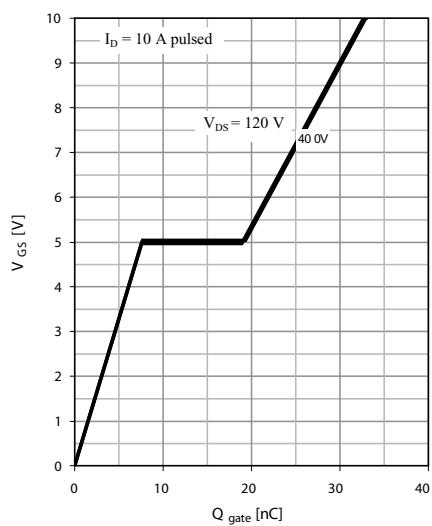


Fig. 8 Typ. gate charge

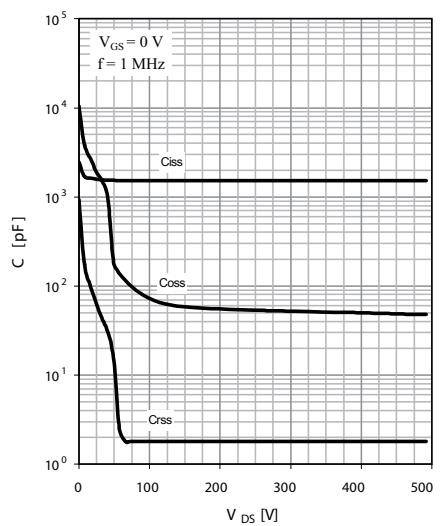


Fig. 9 Typ. capacitances

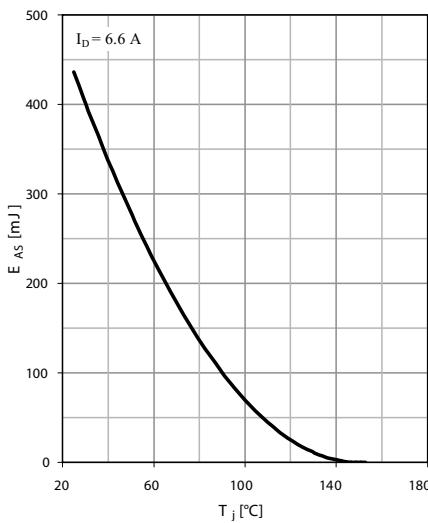


Fig. 10 Avalanche energy

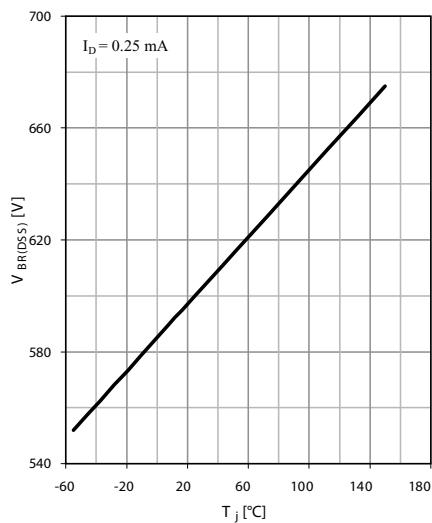


Fig. 11 Drain-source breakdown voltage

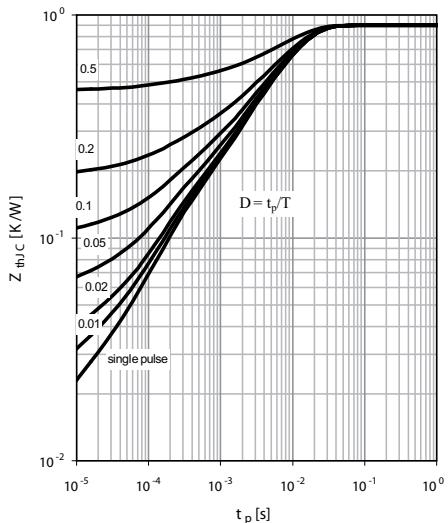


Fig. 12 Max. transient thermal impedance

IXYS reserves the right to change limits, test conditions and dimensions.



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

IXYS:

[IXKP20N60C5](#) [IXKH20N60C5](#)